

2SD1458

Silicon NPN epitaxial planar type

For low-frequency amplification

■ Features

- High forward current transfer ratio h_{FE}
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|---------------------------------------|-----------|-------------|------------------|
| Collector-base voltage (Emitter open) | V_{CBO} | 20 | V |
| Collector-emitter voltage (Base open) | V_{CEO} | 20 | V |
| Emitter-base voltage (Collector open) | V_{EBO} | 15 | V |
| Collector current | I_C | 0.7 | A |
| Peak collector current | I_{CP} | 1.5 | A |
| Collector power dissipation * | P_C | 1 | W |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

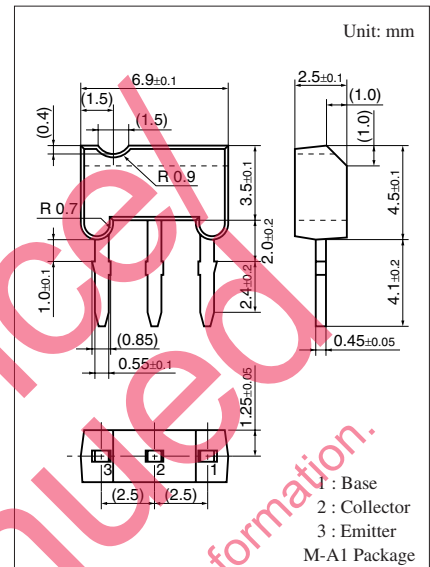
Note) *: Printed circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion

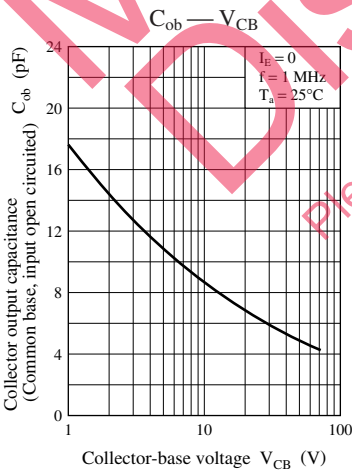
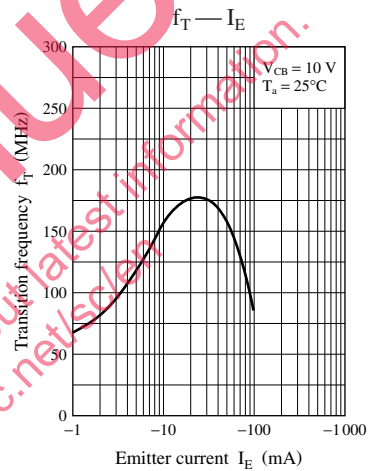
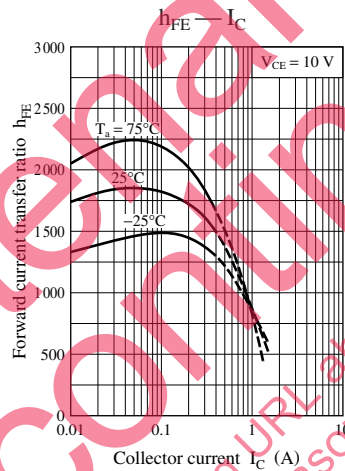
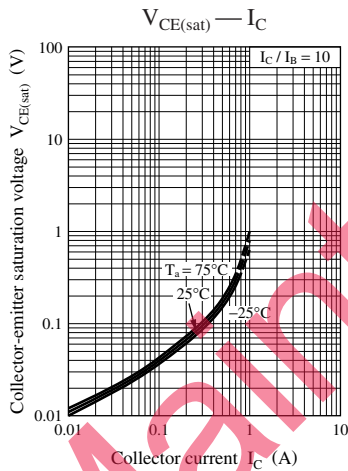
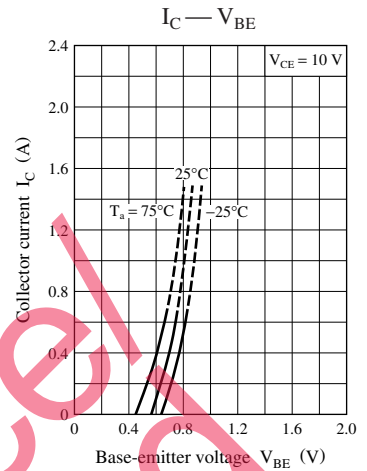
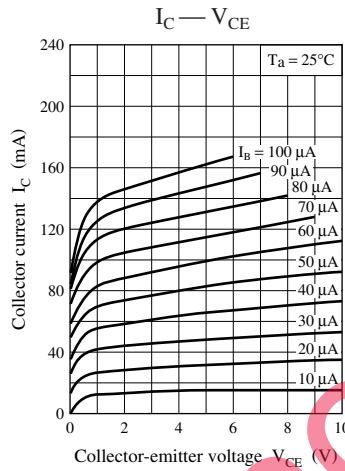
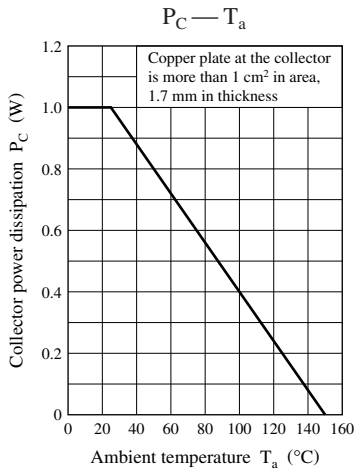
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|---|---------------|--|------|-----|------|---------------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_C = 10 \mu\text{A}, I_E = 0$ | 20 | | | V |
| Collector-emitter voltage (Base open) | V_{CEO} | $I_C = 1 \text{ mA}, I_B = 0$ | 20 | | | V |
| Emitter-base voltage (Collector open) | V_{EBO} | $I_E = 10 \mu\text{A}, I_C = 0$ | 15 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 15 \text{ V}, I_E = 0$ | | | 1 | μA |
| Collector-emitter cutoff current (Base open) | I_{CEO} | $V_{CE} = 15 \text{ V}, I_B = 0$ | | | 10 | μA |
| Forward current transfer ratio | h_{FE} | $V_{CE} = 10 \text{ V}, I_C = 150 \text{ mA}$ | 1000 | | 2500 | — |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ | | | 0.4 | V |
| Transition frequency | f_T | $V_{CB} = 20 \text{ V}, I_E = -20 \text{ mA}, f = 200 \text{ MHz}$ | | 55 | | MHz |
| Collector output capacitance (Common base, input open circuited) | C_{ob} | $V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ | | 11 | 15 | pF |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Pulse measurement





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